

Reg. No.

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**B.E./ B.TECH. DEGREE EXAMINATIONS, MAY 2023**

Second Semester

**PH22252 – PHYSICS OF MATERIALS***(Common to EC, EE)***(Regulation 2022)****TIME: 3 HOURS****MAX. MARKS: 100**

| COURSE OUTCOMES | STATEMENT   | RBT LEVEL |
|-----------------|---|-----------|
| CO 1            | Gain knowledge about conducting properties of materials which is very much useful to the branches of study                                  | 3         |
| CO 2            | Evaluate the concepts of semiconductors   | 3         |
| CO 3            | Inculcate the exposure of the dielectric properties and its applications in various fields.   | 3         |
| CO 4            | Summarize the basics of superconducting and magnetic properties. Explore few of their applications in engineering and technology            | 3         |
| CO 5            | Develop an understanding the characteristics of electronic devices and gain knowledge in designing of logic gates and construction of K-map | 4         |

**PART- A(20x2=40Marks)**

(Answer all Questions)

|   | CO | RBT LEVEL |
|---|----|-----------|
| 1. Mention mean free path in the conducting materials.  | 1  | 2         |
| 2. Devise the way to arrive at microscopic form of Ohm's law.   | 1  | 2         |
| 3. The Fermi temperature of a metal is 24600 K. Calculate the Fermi velocity.   | 1  | 3         |
| 4. Point out the significance of photo electric effect.   | 1  | 2         |
| 5. Distinguish between intrinsic and extrinsic semiconductors.  | 2  | 3         |
| 6. Analyse the significance of compound semiconductors.   | 2  | 2         |
| 7. Mention the applications of Hall effect.   | 2  | 2         |
| 8. Select the junctions of the Schottky diode.  | 2  | 2         |
| 9. Report the difference between dielectric constant and dielectric loss.   | 3  | 3         |
| 10. Corroborate the piezo electricity in dielectric materials.  | 3  | 2         |
| 11. Calculate the electronic polarisability of Neon. The radius of Neon atom is 0.158 nm.<br>(Given $\epsilon_0 = 8.854 \times 10^{-12}$ F/m) | 3  | 3         |
| 12. Enlist the applications of ferroelectric materials.   | 3  | 2         |
| 13. Express the transition temperature in superconductors.  | 4  | 2         |
| 14. Prove that superconductors are perfect diamagnets with the relation, $\chi = -1$ .  | 4  | 3         |
| 15. Sketch the spin arrangement of Para and Ferro magnetic materials.   | 4  | 2         |
| 16. Intervene the significance of magnetic semiconductors.  | 4  | 2         |
| 17. Infer the basic principle of junction field effect transistor.  | 5  | 2         |
| 18. Examine spintronics against the conventional electronics.   | 5  | 2         |
| 19. Analyse the principle of single electron transistor.  | 5  | 2         |
| 20. Interfere the concept of Karnaugh mapping.  | 5  | 3         |

**PART- B(5x 10=50Marks)**

|                |   | Marks       | CO       | RBT<br>LEVEL |
|----------------|---|-------------|----------|--------------|
| <b>21. (a)</b> | Derive the expression for electrical conductivity and thermal conductivity and hence prove Wiedemann-Franz law.                           | <b>(10)</b> | <b>1</b> | <b>3</b>     |
|                | <b>(OR)</b>   |             |          |              |
| <b>(b)</b>     | Derive an expression for density of energy states in metal and hence deduce the expression of Fermi energy at zero Kelvin.                | <b>(10)</b> | <b>1</b> | <b>3</b>     |
| <b>22. (a)</b> | <b>(i)</b> Obtain an expression for the concentration of electrons in the conduction band of an intrinsic semiconductor.                  | <b>(5)</b>  | <b>2</b> | <b>3</b>     |
|                | <b>(ii)</b> With necessary theory describe a method to determine the energy band gap of an intrinsic semiconductor.                       | <b>(5)</b>  | <b>2</b> | <b>3</b>     |
|                | <b>(OR)</b>   |             |          |              |
| <b>(b)</b>     | Describe a theory and experimental procedure for the measurement of the Hall coefficient of a semiconductor and discuss its applications. | <b>(10)</b> | <b>2</b> | <b>3</b>     |
| <b>23. (a)</b> | Arrive at the expression for the local field in a dielectric for a cubic structure and deduce Clausius-Mosotti equation.                  | <b>(10)</b> | <b>3</b> | <b>3</b>     |
|                | <b>(OR)</b>   |             |          |              |
| <b>(b)</b>     | Explain different types of dielectric breakdown mechanisms with remedies.   | <b>(10)</b> | <b>3</b> | <b>3</b>     |
| <b>24. (a)</b> | <b>(i)</b> Compare and contrast between Type-I and Type-II superconductors.   | <b>(5)</b>  | <b>4</b> | <b>4</b>     |
|                | <b>(ii)</b> Concatenate the principle how "MAGLEV" train is made to float above the rails?  | <b>(5)</b>  | <b>4</b> | <b>4</b>     |
|                | <b>(OR)</b>   |             |          |              |
| <b>(b)</b>     | Discuss the various energies involved in domains of ferromagnetic materials and enlighten hysteresis by domain theory.                    | <b>(10)</b> | <b>4</b> | <b>4</b>     |
| <b>25. (a)</b> | Illustrate the working mechanism of JFET with necessary diagram.  | <b>(10)</b> | <b>5</b> | <b>4</b>     |
|                | <b>(OR)</b>   |             |          |              |
| <b>(b)</b>     | Construct any two logic gates using transistor.   | <b>(10)</b> | <b>5</b> | <b>4</b>     |

**PART- C(1x 10=10Marks)**

(Q.No.26 is compulsory)

|            |  | Marks       | CO       | RBT<br>LEVEL |
|------------|--|-------------|----------|--------------|
| <b>26.</b> | Extrapolate the various characteristics of dia, para and ferro magnetic materials. | <b>(10)</b> | <b>4</b> | <b>5</b>     |